

IN THE SPECIFICATION

Please substitute the corresponding paragraph with the following amended paragraph.

In the paragraph starting on page 15, line 4:

In one version, a two-step mask material etch may be performed. For example, a first step may comprise exposing mask material 240 to process gas comprising a composition that is substantially absent a polymer forming gas and the second step may comprise exposing the mask material 240 to process gas having a composition comprising a polymer forming gas. In one particular version, the first mask material etchant gas may comprise a fluorine-containing gas, for example, in one version, the first mask material etchant gas comprises one or more of CF_4 , C_2F_6 , NF_3 , and SF_6 , and the second mask material etchant gas may comprise one or more of CHF_3 , CH_2F_2 , and CH_3F , with or without one or more of CF_4 , C_2F_6 , NF_3 , and SF_6 . The first or second mask material etchant gases may also comprise an inert or carrier gas, such as Ar, He, or N to aid in controlling sputtering and/or dilution. In this version, the etchant residue formed during processing of a previous substrate may be cleaned from the chamber surfaces 275 before polymeric residues are formed and deposited thereon. This can result in easier removal of the etchant deposits. Sandwich deposits comprising a layer of silicon-containing etchant residue and a layer of polymer can be difficult to clean and can result in flaking during substrate processing that can affect the quality of the processing. By first introducing a non-polymerizing mask etching gas, the mask material 240 may be etched and the etchant residue may be cleaned from the chamber surfaces 275 before the polymeric residue is formed and deposited on the chamber surfaces 275. It is advantageous to use the mask material etchant gas comprising polymer forming gas because it aids in etch process performance.